	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
1	BRS	11322	oxynitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 08:40		
2	BRS	329273	nitrogen adj1 rich adj$n plasma	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/10/21 08:41		
3	BRS	5225	oxynitride and (nitrogen adj1 rich adj$n plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 08:42		
4	BRS	5208	(oxynitride and (nitrogen adj1 rich adj$n plasma)) and (nitrogen or plasma or enrich$5 or rich$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 08:42		
5	BRS	1894	((oxynitride and (nitrogen adj1 rich adj$n plasma)) and (nitrogen or plasma or enrich$5 or rich$3)) and (("N.sub.2O") or ("N.sub.2") or ("NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 08:43		
6	BRS	1887	(((oxynitride and (nitrogen adj1 rich adj$n plasma)) and (nitrogen or plasma or enrich$5 or rich$3)) and (("N.sub.2O") or ("N.sub.2") or ("NH.sub.3"))) and (thickness or thick$5 or angstroms or ("N.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 08:45		
7	BRS	158	((((oxynitride and (nitrogen adj1 rich adj$n plasma)) and (nitrogen or plasma or enrich$5 or rich$3)) and (("N.sub.2O") or ("N.sub.2") or ("NH.sub.3"))) and (thickness or thick$5 or angstroms or ("N.sub.2"))) and ONO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 08:46		
8	BRS	158	(((((oxynitride and (nitrogen adj1 rich adj$n plasma)) and (nitrogen or plasma or enrich$5 or rich$3)) and (("N.sub.2O") or ("N.sub.2") or ("NH.sub.3"))) and (thickness or thick$5 or angstroms or ("N.sub.2"))) and ONO) and (plasma or nitrogen or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 08:47		
9	BRS	535681	((((((oxynitride and (nitrogen adj1 rich adj$n plasma)) and (nitrogen or plasma or enrich$5 or rich$3)) and (("N.sub.2O") or ("N.sub.2") or ("NH.sub.3"))) and (thickness or thick$5 or angstroms or ("N.sub.2"))) and ONO) and (plasma or nitrogen or nitride)) or (rich$3 or enrich$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 08:48		
10	BRS	40	((((((oxynitride and (nitrogen adj1 rich adj$n plasma)) and (nitrogen or plasma or enrich$5 or rich$3)) and (("N.sub.2O") or ("N.sub.2") or ("NH.sub.3"))) and (thickness or thick$5 or angstroms or ("N.sub.2"))) and ONO) and (plasma or nitrogen or nitride)) and (rich$3 or enrich$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:12		
11	BRS	5	"6100559"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:12		
12	BRS	1155024	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:29		
13	BRS	62695	semiconductor and (tensil$4 adj$n stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:30		
14	BRS	10546	(semiconductor and (tensil$4 adj$n stress)) and impurit$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:31		
15	BRS	101	((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (dyn$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:32		
16	BRS	942	((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:34		
17	BRS	934	(((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)) and (gas or chlorine or (silicon adj1 nitride) or ("Si.sub.3 N.sub.4") or N or Si or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:36		
18	BRS	404	((((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)) and (gas or chlorine or (silicon adj1 nitride) or ("Si.sub.3 N.sub.4") or N or Si or nitride)) and (mixt$5 or ("SiCl.sub.4") or ("SiH.sub.2 Cl.sub.2") or ("SiCl.sub.3") or ("Si.sub.2 Cl.sub.6"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:40		
19	BRS	402	(((((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)) and (gas or chlorine or (silicon adj1 nitride) or ("Si.sub.3 N.sub.4") or N or Si or nitride)) and (mixt$5 or ("SiCl.sub.4") or ("SiH.sub.2 Cl.sub.2") or ("SiCl.sub.3") or ("Si.sub.2 Cl.sub.6"))) and (Torr or temperature or ratio or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:42		
20	BRS	2	50 and (prssure or get$6 or contact$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 10:46		
21	BRS	398	((((((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)) and (gas or chlorine or (silicon adj1 nitride) or ("Si.sub.3 N.sub.4") or N or Si or nitride)) and (mixt$5 or ("SiCl.sub.4") or ("SiH.sub.2 Cl.sub.2") or ("SiCl.sub.3") or ("Si.sub.2 Cl.sub.6"))) and (Torr or temperature or ratio or element)) and (pressure or get$6 or contact$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 11:37		
22	BRS	392	(((((((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)) and (gas or chlorine or (silicon adj1 nitride) or ("Si.sub.3 N.sub.4") or N or Si or nitride)) and (mixt$5 or ("SiCl.sub.4") or ("SiH.sub.2 Cl.sub.2") or ("SiCl.sub.3") or ("Si.sub.2 Cl.sub.6"))) and (Torr or temperature or ratio or element)) and (pressure or get$6 or contact$6)) and (tens$6 or stress$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 11:58		
23	BRS	0	((((((((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)) and (gas or chlorine or (silicon adj1 nitride) or ("Si.sub.3 N.sub.4") or N or Si or nitride)) and (mixt$5 or ("SiCl.sub.4") or ("SiH.sub.2 Cl.sub.2") or ("SiCl.sub.3") or ("Si.sub.2 Cl.sub.6"))) and (Torr or temperature or ratio or element)) and (pressure or get$6 or contact$6)) and (tens$6 or stress$4)) and (dyne)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 11:58		
24	BRS	55	((((((((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)) and (gas or chlorine or (silicon adj1 nitride) or ("Si.sub.3 N.sub.4") or N or Si or nitride)) and (mixt$5 or ("SiCl.sub.4") or ("SiH.sub.2 Cl.sub.2") or ("SiCl.sub.3") or ("Si.sub.2 Cl.sub.6"))) and (Torr or temperature or ratio or element)) and (pressure or get$6 or contact$6)) and (tens$6 or stress$4)) and tensile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 12:35		

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
25	BRS	6	(((((((((semiconductor and (tensil$4 adj$n stress)) and impurit$4) and (LPCVD)) and (gas or chlorine or (silicon adj1 nitride) or ("Si.sub.3 N.sub.4") or N or Si or nitride)) and (mixt$5 or ("SiCl.sub.4") or ("SiH.sub.2 Cl.sub.2") or ("SiCl.sub.3") or ("Si.sub.2 Cl.sub.6"))) and (Torr or temperature or ratio or element)) and (pressure or get$6 or contact$6)) and (tens$6 or stress$4)) and tensile) and (dyn$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 12:36		